

L Number	Hits	Search Text	DB	Time stamp
-	19557	contact adj pad	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/14 10:55
-	0	oxidation adj resistance near4 (contact adj pad)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/21 13:31
-	7973	oxidation adj resistant	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/21 13:34
-	3	(oxidation adj resistant) near4 (contact adj pad)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/21 13:32
-	21288	oxidation adj resistant or oxidation adj resistance	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/21 13:34
-	134	wire near4 (oxidation adj resistant or oxidation adj resistance)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/21 13:37
-	17	semiconductor and (wire near4 (oxidation adj resistant or oxidation adj resistance))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/21 13:38
-	25169	wire adj bonding	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/21 13:39
-	11	(contact adj pad) and (oxidation adj resistant or oxidation adj resistance) and (wire adj bonding)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/21 13:42
-	1556	(438/106).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/12/12 16:12
-	2	(oxidation adj resistant or oxidation adj resistance) and (("438/106").CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/21 13:44
-	111	gold adj contact adj pad	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/21 13:45
-	5035	gold adj wire	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/21 13:45
-	15	(gold adj contact adj pad) and (gold adj wire)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/21 13:45

-	64114	semiconductor adj chip	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/12/12 16:12
-	97	(semiconductor adj chip) and "chip-on-chip"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/12/12 16:13
-	188	"chip-on-chip"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/12/12 16:36
-	1112	(257/690).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/12/12 16:45
-	605	(257/777).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/12/12 16:50
-	1023929	wire	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/12/12 16:51
-	368	((257/777).CCLS.) and wire	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/12/12 16:51
-	5164	connection adj pad	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/12/12 16:51
-	30	((257/777).CCLS.) and wire) and (connection adj pad)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/12/12 16:53
-	322387	corrosion or corrode or corroded	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/12/12 16:54
-	1722415	resistance	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/12/12 16:54
-	37	(semiconductor adj chip) and wire and (connection adj pad) and (corrosion or corrode or corroded) and resistance	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/12/12 16:55
-	2060	contact adj pad and semiconductor adj chip	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/12/12 17:40
-	55468	bump or bumps	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/14 10:56

-	721	(contact adj pad and semiconductor adj chip) and (bump or bumps)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/12/12 17:41
-	365567	insulative or insulation or dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/12/12 17:42
-	676	"7" and ((contact adj pad and semiconductor adj chip) and (bump or bumps))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/12/12 17:43
-	1722415	resistance	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/12/12 17:43
-	342	("7" and ((contact adj pad and semiconductor adj chip) and (bump or bumps))) and resistance	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/14 10:53
-	7	5587337.URPN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/12/12 17:58
-	174	(257/694).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/12/12 18:08
-	276	(257/673).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/12/12 18:12
-	806	(257/686).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/12/12 18:36
-	917	(257/737).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/12/12 18:37
-	8	5587337.URPN.	USPAT	2002/11/14 10:52
-	3335	((flip adj chip or mcm or csp) and (oxidation adj resistant or oxidation resistance) and wire)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/14 10:55
-	63351	bump or bumps and (contact adj pad and ((flip adj chip or mcm or csp) and (oxidation adj resistant or oxidation resistance) and wire)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/14 10:56
-	767	contact adj pad and (((flip adj chip or mcm or csp) and (oxidation adj resistant or oxidation resistance) and wire))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/14 10:57
-	1418	(257/690).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/13 09:16

-	197	internal and external and ((257/690).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/13 09:18
-	1096	(257/777).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/13 09:18
-	228	internal and external and ((257/777).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/13 09:22
-	1096	(257/777).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/13 09:22